

Date/hour	No	type	Title	Author
November 17th 2013 (Sunday)				
20:00	Welcome glass of wine Hotel Qubus			
November 18th 2013 (Monday)				
8:30-8:40	Conference opening			
8:40-9:10	Mo1	I1	<i>Emission characteristics of InGaN-based regularly arranged nanocolumn arrays</i>	Katsumi Kishino Sophia University, Japan
9:10-9:40	Mo2	I2	<i>Progress in nonpolar and semipolar GaN-based laser diodes</i>	Dan Cohen, UCSB, USA
9:40-9:55	Mo3	C1	<i>Cyan AlGaIn-cladding free nitride laser diodes grown by PAMBE</i>	Henryk Turski Unipress, Poland
9:55-10:10	Mo4	C2	<i>Effect of index-antiguinding on the lasing threshold of narrow RW (In,Al)GaIn laser diodes investigated by self-consistent simulations</i>	Luca Radaelli Ferdinand Braun Institute, Germany
10:10-10:25	Mo5	C3	<i>InGaIn GRINSCH laser diodes</i>	Szymon Stańczyk Unipress, Poland
10:25-11:00	Coffee break			
11:00-11:30	Mo6	I3	<i>Long wavelength VCSELs and VECSELs made by wafer fusion</i>	Elyahou Kapon EPFL, Switzerland
11:30-12:00	Mo7	I4	<i>High power femtosecond pulse vertical-external-cavity surface-emitting lasers</i>	Keith Wilcox University of Southampton, UK
12:00-12:15	Mo8	C4	<i>Switchable, two wavelength emitting VECSEL</i>	Artur Broda ITE, Poland
12:15-12:30	Mo9	C5	<i>GaAs/AlO_x high contrast gratings for 980 nm VCSELs</i>	Marcin Gębski Lodz Technical University, Poland
13:00-14:30	Lunch			
14:30-15:00	Mo10	I5	<i>MBE growth and optimization of THz quantum cascade lasers</i>	Zbig Wasilewski University of Waterloo, Canada
15:00-15:30	Mo11	I6	<i>II-VI/III-N micro-chip laser diode converters</i>	Sergey Ivanov Ioffe Institute, Russia
15:30-15:45	Mo12	C6	<i>Doping versus threshold current in mid-IR QCL - a NEGF model</i>	Andrzej Kolek Rzeszow University of Technology, Poland
15:45-16:00	Mo13	C7	<i>Application of pressure-tuned laser diodes in spectroscopy</i>	Witold Trzeciakowski Unipress, Poland
16:30-18:30	Poster session - beer			

November 19th 2013 (Tuesday)				
9:00-9:30	Tue1	I7	<i>Progress toward optimizing 850 nm and 980 nm vertical cavity surface emitting lasers (VCSELs) for optical interconnects</i>	James Lott TU Berlin, Germany
9:30-10:00	Tue2	I8	<i>Subwavelength high contrast grating mirrors for applications in vertical-cavity surface-emitting lasers</i>	Maciej Dems Lodz University of Technology, Poland
10:00-10:15	Tue3	C8	<i>Numerical simulation of optical properties of long-wavelength wafer-fused VCSELs with intra-cavity patterning</i>	Tomasz Czystanowski Lodz University of Technology, Poland
10:00-10:30	Tue4	C9	<i>Semiconductor double-chirped mirrors for dispersion compensation in femtosecond Yb:KYW lasers</i>	Łukasz Zinkiewicz Physics Department Warsaw University, Poland
10:30-11:00	Coffee break			

11:00-11:30	Tue5	I9	<i>Future light sources for pico projection</i>	Jelena Ristic Osram OS, Germany
11:30-12:00	Tue6	I10	<i>UV lasers – status and prospects</i>	Michael Kneissl TU Berlin, Germany
12:00-12:15	Tue7	C10	<i>High power InGaN superluminescent diodes</i>	Anna Kafar Unipress, Poland
12:15-12:30	Tue8	C11	<i>GaN-based ridge waveguide laser diodes: optimizing the optical mode profile</i>	Katarzyna Holc Fraunhofer IAF, Germany
12:30-12:45	Tue9	C12	<i>Thermal stability of InGaN laser diodes</i>	Agata Bojarska Unipress, Poland
13:00-14:30	Lunch			
14:30-15:00	Tue10	I11	<i>High performance AllInGaAs transmission lasers for FTTX applications</i>	Wyn Meredith CST Global, Scotland
15:00-15:30	Tue11	I12	<i>Excitation of 2D plasma waves in semiconductor quantum well and its effect on lasing in InGaN diodes.</i>	Igor Smetanin Lebedev Institute, Russia
15:30-15:45	Tue12	C13	<i>Improved upper heat stream removal in high-power laser diodes using graphene oxide layers</i>	Andrzej Małag ITME, Poland
15:45-16:00	Tue13	C14	<i>High-power laser diodes with multi-stripe-gain distribution</i>	Grzegorz Sobczak ITME, Poland
16:00-16:15	Tue14	C15	<i>Strain compensated 4.7 μm AllInAs/InGaAs/InP QCLs – Non-equilibrium Green's function modeling of electro-optical characteristics</i>	Maciej Bugajski ITE, Poland
19:00-24:00	Conference Dinner			

November 20th 2013 (Wednesday)				
9:00-9:30	Wed1	I13	<i>Combining MOVPE & low-temperature MBE for efficient green laser diodes</i>	Lise Lahourcade EPFL, Switzerland
9:30-10:00	Wed2	I14	<i>Picosecond pulse generation in GaN-baser laser diodes</i>	Ulrich Schwarz University of Freiburg, Germany
10:0-10:15	Wed3	C16	<i>Optical simulations of InGaN/GaN edge emitting lasers with reduced AlGaIn cladding thickness</i>	Tomasz Czystanowski Lodz University of Technology, Poland
10:15-10:30	Wed4	C17	<i>Far field pattern of AlGaIn cladding free blue laser diodes grown by PAMBE</i>	Grzegorz Muzioł Unipress, Poland
10:30-11:00	Coffee break			
11:00-11:30	Wed5	I15	<i>Type II quantum well structures for mid-infrared emitting interband cascade lasers: challenges, limitations and prospects</i>	Grzegorz Sęk Wroclaw University of Technology, Poland
11:30-12:00	Wed6	I16	<i>(AlGaIn)N-based laser diodes: future applications and present problems</i>	Michał Leszczyński TopGaN Ltd., Poland
12:00-12:15	Wed7	C18	<i>GaN laser diodes for systems applications</i>	Steve Najda TopGaN Ltd., Poland
12:15-12:30	Wed8	C19	<i>Power limits of III-N-based single and multi emitter laser diodes</i>	Maciej Kuc Lodz University of Technology, Poland
12:30-12:45	Wed9	C20	<i>Hydrostatic pressure tuning of emission wavelength and optical gain in GaInNAs/GaAs quantum wells</i>	Marta Gładysiewicz - Kudrawiec Wroclaw University of Technology, Poland
12:45-13:00	Wed10	C21	<i>Pressure studies of leakage in laser diodes</i>	Artem Bercha Unipress, Warsaw, Poland
13:00-13:10	Closing remarks			

Poster presentations November 18th 4-6 PM.

Po1	<i>Numerical analysis of mid-ir quantum cascade laser optical properties</i>	Piotr Karbownik ITE, Poland
Po2	<i>Dedicated quantum cascade laser driver</i>	Artur Trajnerowicz ITE, Poland
Po3	<i>MBE growth of VECSEL heterostructures: the challenge of control of the layer thickness and the strain relaxation</i>	Jan Muszalski ITE, Poland
Po4	<i>Full-physical simulation of the novel on-axis pumped VECSEL with High Contrast Grating</i>	Jarosław Walczak Lodz University of Technology Poland
Po5	<i>Numerical modeling of optical properties of vertical-external-cavity surface-emitting lasers</i>	Adam Sokół Lodz University of Technology Poland
Po6	<i>Fabrication of THz quantum cascade lasers</i>	Anna Szerling ITE, Poland
Po7	<i>Epitaxy of AlGaAs/GaAs structures for THz quantum-cascade lasers</i>	Kamil Kosiel ITE, Poland
Po8	<i>Computer simulation of operation of GaN/AlGaIn quantum well ultraviolet diode laser</i>	Łukasz Piskorski Lodz University of Technology Poland
Po9	<i>Spin orbit splitting in InGaAsSb/InAs layers for heterojunction lasers</i>	Mateusz Dyksik Wroclaw University of Technology, Poland
Po10	<i>Optical characterization of InAs-substrate-based type II quantum wells for long-wavelength mid-infrared interband cascade laser with plasmon waveguiding enhancement</i>	Filip Janiak Wroclaw University of Technology, Poland
Po11	<i>Coupling of multiple laser diodes into a fiber</i>	Yurii Ivonyak Unipress, Poland
Po12	<i>Optical properties of AlGaAsGaAs superlattices for quantum cascade lasers for mid infrared and terahertz range</i>	Marcin Motyka Wroclaw University of Technology, Poland
Po13	<i>Investigating up-conversion phenomena in active glasses using pressure-tuned laser diodes</i>	Ryszard Piramidowicz Warsaw University of Technology, Poland
Po14	<i>Photonic integrated circuits for application in multi-wavelength communication systems</i>	Stanisław Stopiński Warsaw University of Technology, Poland
Po15	<i>Tuning of InGaN/GaN laser diodes band structure by hydrostatic pressure</i>	Jakub Goss Unipress, Poland
Po16	<i>Thermal characteristics and power roll-over of GaAs/AlGaAs quantum cascade lasers</i>	Kamil Pierściński ITE, Poland
Po17	<i>Wafer fused VECSELS emitting in 1.3 μm and 1.5 μm range</i>	Kamil Pierściński ITE, Poland